

INFORMATION DISCLOSURE CITATION PTO-1449		Customer Number: 26615	ATTORNEY'S DKT NO. H1442		APPLICATION No. Unassigned 10/728, 910		
			APPLICANT(S) Wiley Eugene Hill et al.				
			FILING DATE December 8, 2003		GROUP Unassigned 2818		
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
TH	4,996,574	02-26-91	Shirasaki	357	23.7	06-30-89	
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
TH	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.						
	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.						
	Xuejue Huang et al., "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.						
	Xuejue Huang et al., "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70.						
TH	Yang-Kyu Choi et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.						
TH	Co-pending U.S. Application Serial No. 10/638,334, filed August 12, 2003, entitled: "Systems and Methods for Forming Dense N-Channel and P-Channel Fins Using Shadow Implantation," 16 page specification, 18 sheets of drawings.						
TH	Co-pending U.S. Application Serial No. 10/429,697, filed May 6, 2003, entitled: "FinFET-Based SRAM Cell," 16 page specification, 12 sheets of drawings.						
EXAMINER TH TH TH			DATE CONSIDERED Oct 04				

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).